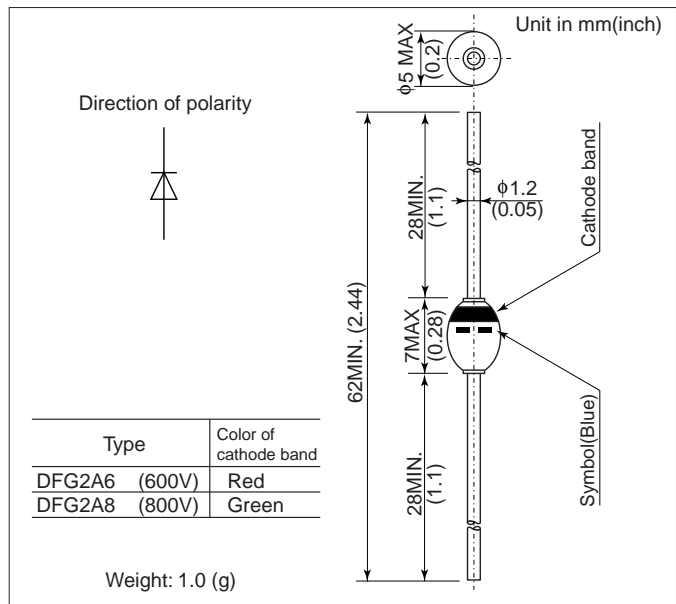


DFG2A

FEATURES

- For high speed switching.
- Diffused-junction. Glass passivated and encapsulated.

OUTLINE DRAWING



ABSOLUTE MAXIMUM RATINGS

| Items | Type | | DFG2A6 | DFG2A8 |
|---------------------------------------|------------------|------------------|---|--------|
| Repetitive Peak Reverse Voltage | V_{RRM} | V | 600 | 800 |
| Average Forward Current | $I_{F(AV)}$ | A | 2.5 (Single-phase half sine wave 180° conduction) TL = 80°C, Lead length = 10mm | |
| Surge(Non-Repetitive) Forward Current | I_{FSM} | A | 80 (Without PIV, 10ms conduction, Tj = 165°C start) | |
| I ² t Limit Value | I ² t | A ² s | 25.6 (Time = 2 ~ 10ms, I = RMS value) | |
| Operating Junction Temperature | T _j | °C | -65 ~ +165 | |
| Storage Temperature | T _{stg} | °C | -65 ~ +165 | |

Notes (1) Lead mounting : Lead temperature 300°C max. to 3.2mm from body for 5sec. max..

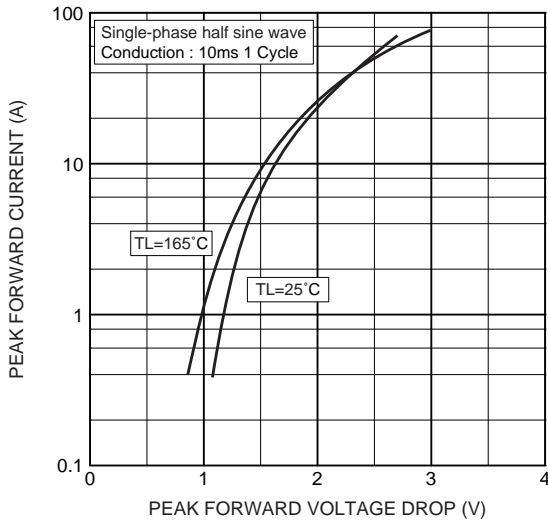
(2) Mechanical strength : Bending 90°×2 cycles or 180°×1 cycle, Tensile 3kg, Twist 90°×1 cycle.

CHARACTERISTICS(T_L=25°C)

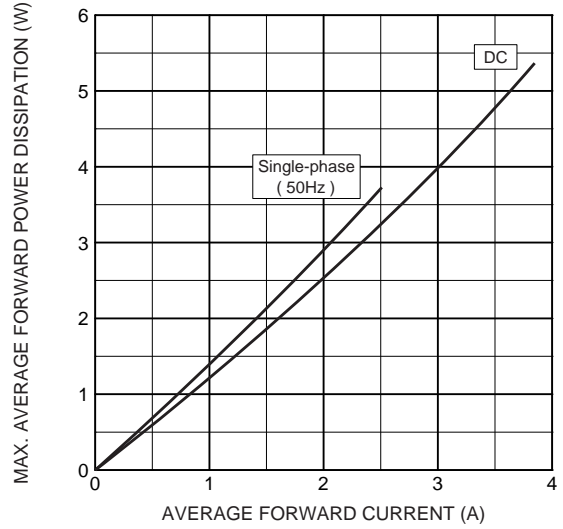
| Items | Symbols | Units | Min. | Typ. | Max. | Test Conditions |
|--------------------------------|---------------|-------|------|------|------|---|
| Peak Reverse Current | I_{RRM} | μA | — | — | 10 | Rated V_{RRM} |
| Peak Forward Voltage | V_{FM} | V | — | — | 1.3 | $I_{FM}=2.5A_p$, Single-phase half sine wave 1 cycle |
| Reverse Recovery Time | t_{rr} | μs | — | — | 0.2 | $I_F=0.5A$, $I_{rp}=1.0A$, 25% Recovery |
| Steady State Thermal Impedance | $R_{th(j-a)}$ | °C/W | — | — | 50 | Lead length = 10 mm |
| | $R_{th(j-l)}$ | | | | 20 | |

DFG2A

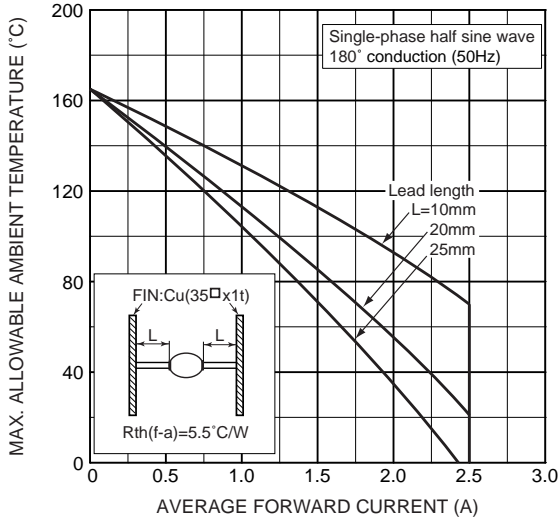
Forward characteristics



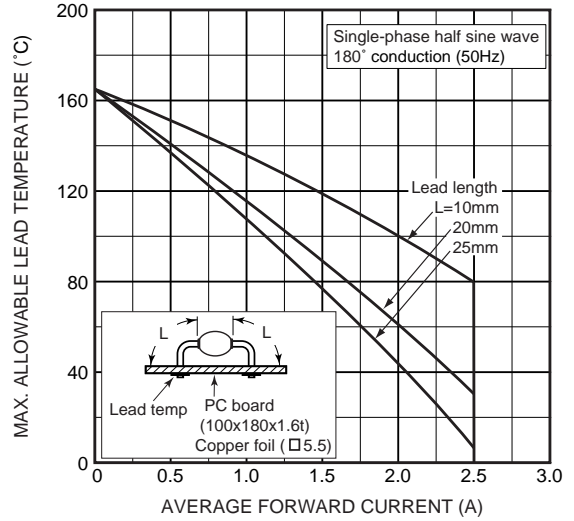
Max. average forward power dissipation (Resistive or inductive load)



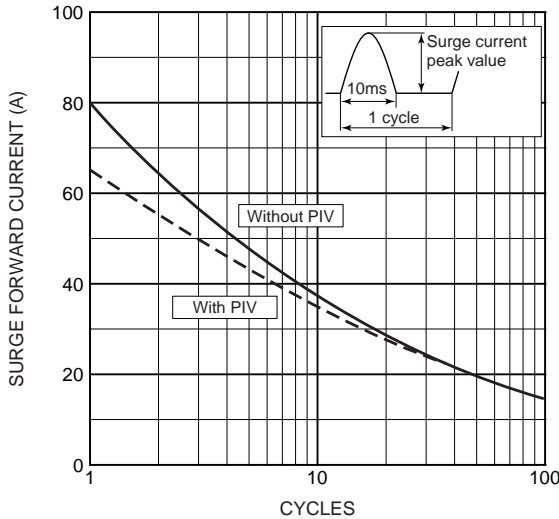
Max. allowable ambient temperature (Resistive or inductive load)



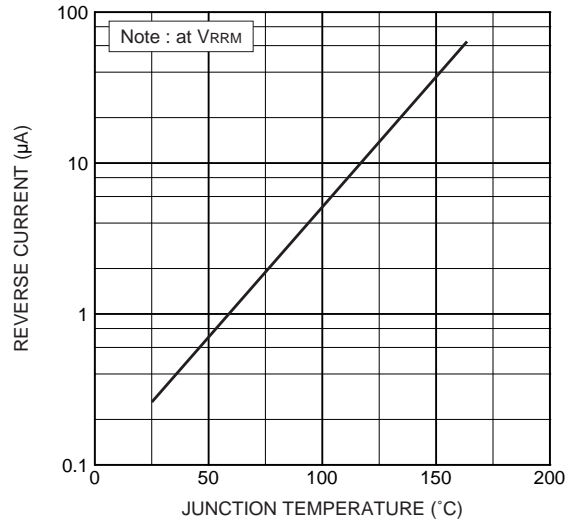
Max. allowable lead temperature (Resistive or inductive load)



Surge forward current characteristics (Non-repetitive)

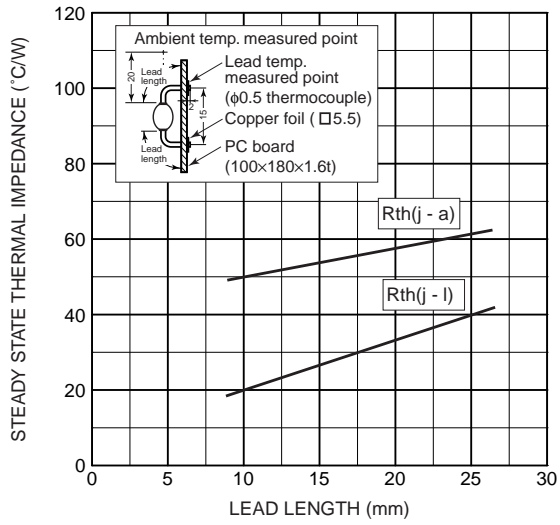


Typ. Reverse current vs. junction temperature

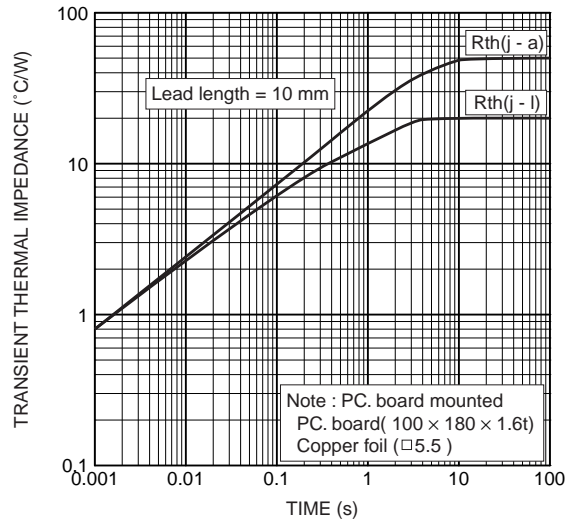


DFG2A

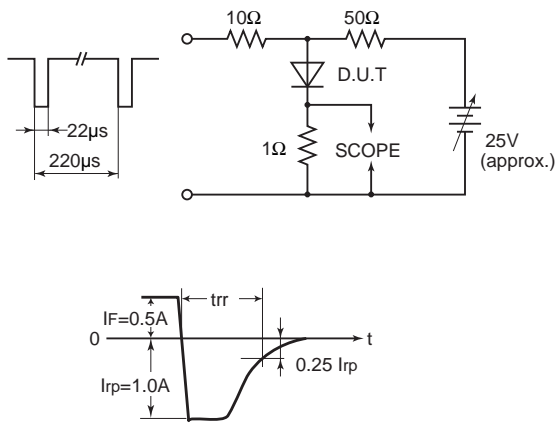
Steady state thermal impedance



Transient thermal impedance



Reverse recovery time (trr) test circuit



Precautions for Safe Use and Notices

If semiconductor devices are handled in inappropriate manner, failures may result. For this reason, be sure to read "Precaution for Use" before use.



This mark indicates an item about which caution is required.



CAUTION

This mark indicates a potentially hazardous situation which, if not avoided, may result in minor or moderate injury and damage to property.



CAUTION

- (1) Regardless of changes in external conditions during use "absolute maximum ratings" should never be exceed in designing electronic circuits that employ semiconductors. In the case of pulse use, furthermore, "safe operating area(SOA)" precautions should be observed.
- (2) Semiconductor devices may experience failures due to accident or unexpected surge voltages. Accordingly, adopt safe design features, such as redundancy or prevention of erroneous action, to avoid extensive damage in the event of a failure.
- (3) In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, life-support-related medical equipment, fuel control equipment and various kinds of safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of user's fail-safe precautions or other arrangement. Or consult Hitachi's sales department staff.

(If a semiconductor device fails, there may be cases in which the semiconductor device, wiring or wiring pattern will emit smoke or cause a fire or in which the semiconductor device will burst)

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